SINGLE DAMASCENE METHOD FOR RF IC PASSIVE COMPONENT INTEGRATION IN COPPER INTERCONNECT PROCESS

The present invention relates to a method of integrating copper inductor, MIM capacitor and precision resistors in a copper IC fabrication process. The method requires minimal modifications to conventional copper damascene interconnect processes and uses as few as two additional masking layers to create the inductor, resistor and capacitor, for example.

(Fig. 1)

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